

Parametri 180 nm CMOS tehnološkog procesa

Izvor: https://www.mosis.com/cgi-bin/cgiwrap/umosis/swp/params/tsmc-018/t3az_lo_epi-params.txt

$$\lambda=0,09\mu\text{m},$$

$$V_{DD}=1,8\text{ V}, V_{TN}=|V_{TP}|=0,53\text{ V}, V_{DSATn}=0,34\text{ V}, V_{DSATp}=-0,63\text{ V},$$

$$\lambda_{CLM,NMOS}=0,06\text{ V}^{-1}, \lambda_{CLM,PMOS}=-0,1\text{ V}^{-1}, \text{CLM} - \text{Channel Length Modulation}$$

$$k'_n=334,8\text{ }\mu\text{A/V}^2, k'_p=-71,2\text{ }\mu\text{A/V}^2, C_{ox}=8,42\text{ fF}/\mu\text{m}^2,$$

$$R_{eq,N/sq}=9,88\text{ k}\Omega/\square, R_{eq,P/sq}=27,1\text{ k}\Omega/\square,$$

$$C_{A,poly-sub}=98\text{ aF}/\mu\text{m}^2, C_{A,m1-sub}=38\text{ aF}/\mu\text{m}^2, C_{A,m2-sub}=19\text{ aF}/\mu\text{m}^2, C_{A,m3-sub}=13\text{ aF}/\mu\text{m}^2,$$

$$C_{A,m4-sub}=8\text{ aF}/\mu\text{m}^2, C_{A,m5-sub}=8\text{ aF}/\mu\text{m}^2, C_{A,m6-sub}=3\text{ aF}/\mu\text{m}^2, C_{A,N+-sub}=986\text{ aF}/\mu\text{m}^2,$$

$$C_{A,P+-sub}=1134\text{ aF}/\mu\text{m}^2,$$

$$C_{F,poly-sub}=? - \text{zanemaruje se}, C_{F,m1-sub}=14\text{ aF}/\mu\text{m}, C_{F,m2-sub}=59\text{ aF}/\mu\text{m}, C_{F,m3-sub}=53\text{ aF}/\mu\text{m},$$

$$C_{F,m4-sub}=42\text{ aF}/\mu\text{m}, C_{F,m5-sub}=24\text{ aF}/\mu\text{m}, C_{F,m6-sub}=? - \text{zanemaruje se}, C_{F,N+-sub}=248\text{ aF}/\mu\text{m},$$

$$C_{F,P+-sub}=208\text{ aF}/\mu\text{m},$$

$$r_{poly}=7,9\text{ }\Omega/\square, r_{m1}=0,08\text{ }\Omega/\square, r_{m2}=0,08\text{ }\Omega/\square, r_{m3}=0,08\text{ }\Omega/\square, r_{m4}=0,07\text{ }\Omega/\square, r_{m5}=0,07\text{ }\Omega/\square,$$

$$r_{m6}=0,03\text{ }\Omega/\square$$